

Notice of References CitedApplication/Control No.
10/062,776Applicant(s)/Patent Under Reexam
Yoshiyuki et alExaminer
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2812

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¹ A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.